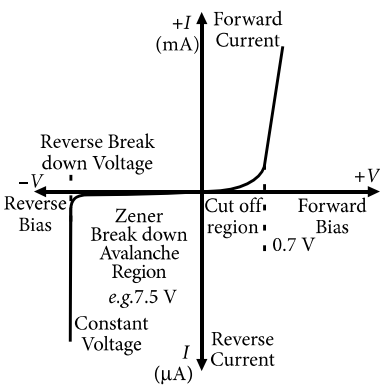


## TYPES OF SEMICONDUCTORS

### INTRINSIC SEMICONDUCTORS

The pure semiconductors have thermally generated current carriers. Here,  $n_e = n_h = n_i$



### APPLICATIONS OF DIODE

- **Diode as a rectifier**
  - Half wave rectifier
  - Full wave rectifier
- **Zener diode** as a voltage regulator.
- **Photo diode** for detecting light signals.
- **LED:** light emitting diode.
- **Solar cells:** Generates emf from solar radiations.

### EXTRINSIC SEMICONDUCTORS

The semiconductor whose conductivity is mainly due to doping of impurity.

#### p-type semiconductor

- Doped with trivalent atom.
- Here,  $n_h \gg n_e$

#### n-type semiconductor

- Doped with pentavalent atom.
- Here,  $n_e \gg n_h$

### SEMICONDUCTOR DIODE

**p-n junction diode :** A p-type semiconductor is brought into contact with an n-type semiconductor such that structure remains continuous at boundary.

### BIASING CHARACTERISTICS

#### Forward bias characteristic

- Width of depletion layer decreases
- Effective barrier potential decreases
- Low resistance at junction
- High current flow of the order of mA.

#### Reverse bias characteristic

- Width of depletion layer increases
- Effective barrier potential increases
- High resistance at the junction
- Low current flow of the order of  $\mu A$ .
- Reverse break down occurs at a high reverse bias voltage.

### JUNCTION TRANSISTOR

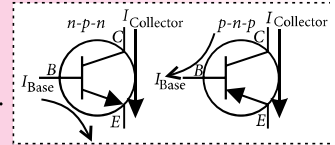
A semiconductor device possessing fundamental action of transfer resistor.

#### Junction transistors are of two types

- **n-p-n transistor:** A thin layer of p-type semiconductor is sandwiched between two n-type semiconductors.
- **p-n-p transistor:** A thin layer of n-type semiconductor is sandwiched between two p-type semiconductors.

#### There are three configurations of transistors

- CB (Common Base)
- CE (Common Emitter)
- CC (Common Collector).



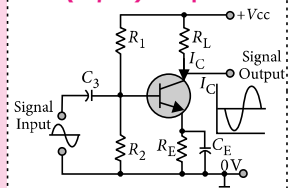
#### Transistor characteristics

- Input resistance  $(r_i)_{(CE)} = \left( \frac{\Delta V_{BE}}{\Delta I_B} \right)_{V_{CE} = \text{constant}}$
- Output resistance  $(r_o)_{(CE)} = \left( \frac{\Delta V_{CE}}{\Delta I_C} \right)_{I_B = \text{constant}}$
- Current amplification factor  $\beta_{ac} = \left( \frac{\Delta I_C}{\Delta I_B} \right)_{V_{CE} = \text{constant}}$  and  $\alpha_{ac} = \left( \frac{\Delta I_C}{\Delta I_E} \right)_{V_{CB} = \text{constant}}$

### APPLICATIONS OF TRANSISTOR

- **Transistor as an Amplifier**
  - Its operating voltage is fix in active region.
  - Voltage gain,  $A_v = \frac{V_o}{V_i} = -\beta_{ac} \frac{R_{out}}{R_{in}}$
  - Power gain,  $A_p = A_v \times \beta_{ac}$
- **Transistor as a Switch**
- **Transistor as an Oscillator**

#### CE(n-p-n) Amplifier



## DIGITAL ELECTRONICS AND LOGIC GATES

### VARIOUS TYPES OF LOGIC GATE

#### AND Gate

Output is high only when both inputs are high.

A	B	Y
0	0	0
0	1	0
1	0	0
1	1	1

$Y = A \cdot B$

#### OR Gate

Output is high if any one or both inputs are high.

A	B	Y
0	0	0
0	1	1
1	0	1
1	1	1

$Y = A + B$

#### NOT Gate

It just inverts the input signal.

A	Y
0	1
1	0

$Y = \bar{A}$

#### NAND Gate

An AND Gate followed by a NOT Gate.

A	B	Y
0	0	1
0	1	1
1	0	1
1	1	0

$Y = \overline{A \cdot B}$

#### NOR Gate

An OR Gate followed by a NOT Gate.

A	B	Y
0	0	1
0	1	0
1	0	0
1	1	0

$Y = \overline{A + B}$